
(Poster)

OKI SOI technology evaluation

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The CMOS transistors of the silicon-on-insulator (SOI) technology has a number of advantages over of the standard bulk CMOS technology, such as no latch-up effect, low junction capacitance for high speed and low power, etc. A fully depleted SOI (FD-SOI) technology provided by OKI Electronics Co. ltd is realizing the full feature of the advantages. Test element group (TEG) structures of transistors were designed and fabricated to evaluate the influences of radiation to the transistors. Results from pre- and post-irradiation will be presented.